

# TLP731, TLP732

OFFICE MACHINE  
 HOUSEHOLD USE EQUIPMENT  
 SOLID STATE RELAY  
 SWITCHING POWER SUPPLY

The TOSHIBA TLP731 and TLP732 consist of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

TLP732 is no-base internal connection for high-EMI environments.

- Collector-Emitter Voltage : 55V (Min.)
- Current Transfer Ratio : 50% (Min.)  
     Rank GB : 100% (Min.)
- UL Recognized : UL1577, File No. E67349
- BSI Approved : BS EN60065 : 1994  
     Certificate No. 6617  
     BS EN60950 : 1992  
     Certificate No. 7366

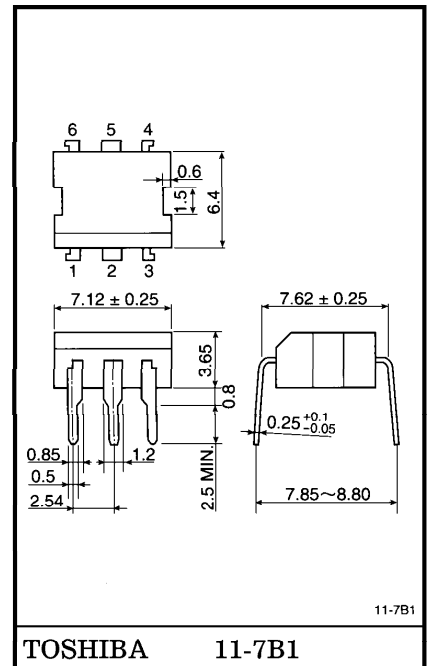
Isolation Voltage : 4000V<sub>rms</sub> (Min.)

- Option (D4) type  
     VDE Approved : DIN VDE0884 / 08.87,  
     Certificate No. 65640  
     Maximum Operating Insulation Voltage : 630V<sub>PK</sub>  
     Highest Permissible Over Voltage : 6000V<sub>PK</sub>

(Note) When a VDE0884 approved type is needed, please designate the "Option (D4)"

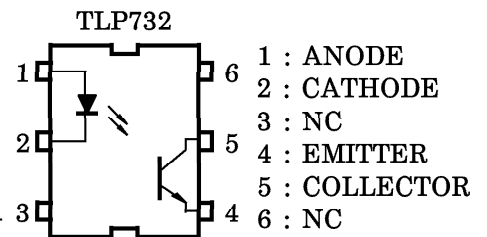
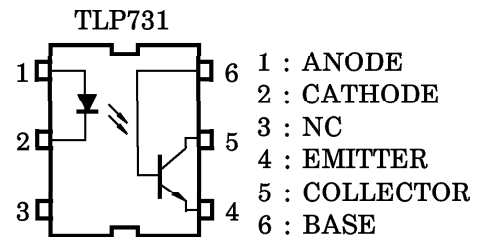
	7.62mm pich standard type	10.16mm pich (LF2) type
● Creepage Distance	: 7.0mm (Min.)	8.0mm (Min.)
Clearance	: 7.0mm (Min.)	8.0mm (Min.)
Insulation Thickness	: 0.5mm (Min.)	0.5mm (Min.)

Unit in mm



Weight : 0.35g

**PIN CONFIGURATIONS (TOP VIEW)**



## MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current	I <sub>F</sub>	60	mA
	Forward Current Derating (Ta ≥ 39°C)	ΔI <sub>F</sub> /°C	-0.7	mA/°C
	Peak Forward Current (100μs pulse, 100pps)	I <sub>FP</sub>	1	A
	Power Dissipation	P <sub>D</sub>	100	mW
	Power Dissipation Derating (Ta ≥ 25°C)	ΔP <sub>D</sub> /°C	-1.0	mW/°C
	Reverse Voltage	V <sub>R</sub>	5	V
	Junction Temperature	T <sub>j</sub>	125	°C
DETECTOR	Collector-Emitter Voltage	V <sub>CEO</sub>	55	V
	Collector-Base Voltage (TLP731)	V <sub>CB0</sub>	80	V
	Emitter-Collector Voltage	V <sub>ECO</sub>	7	V
	Emitter-Base Voltage (TLP731)	V <sub>EBO</sub>	7	V
	Collector Current	I <sub>C</sub>	50	mA
	Power Dissipation	P <sub>C</sub>	150	mW
	Power Dissipation Derating (Ta ≥ 25°C)	ΔP <sub>C</sub> /°C	-1.5	mW/°C
	Junction Temperature	T <sub>j</sub>	125	°C
Storage Temperature Range		T <sub>stg</sub>	-55~125	°C
Operating Temperature Range		T <sub>opr</sub>	-55~100	°C
Lead Soldering Temperature (10s)		T <sub>sol</sub>	260	°C
Total Package Power Dissipation		P <sub>T</sub>	250	mW
Total Package Power Dissipation Derating (Ta ≥ 25°C)		ΔP <sub>T</sub> /°C	-2.5	mW/°C
Isolation Voltage (AC, 1 min., R.H. ≤ 60%)		BV <sub>S</sub>	4000	V <sub>rms</sub>

## RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V <sub>CC</sub>	—	5	24	V
Forward Current	I <sub>F</sub>	—	16	25	mA
Collector Current	I <sub>C</sub>	—	1	10	mA
Operating Temperature	T <sub>opr</sub>	-25	—	85	°C

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	$V_F$	$I_F = 10\text{mA}$	1.0	1.15	1.3	V
	Reverse Current	$I_R$	$V_R = 5\text{V}$	—	—	10	$\mu\text{A}$
	Capacitance	$C_T$	$V = 0, f = 1\text{MHz}$	—	30	—	pF
DETECTOR	Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 0.5\text{mA}$	55	—	—	V
	Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector-Base Breakdown Voltage (TLP731)	$V_{(BR)CBO}$	$I_C = 0.1\text{mA}$	80	—	—	V
	Emitter-Base Breakdown Voltage (TLP731)	$V_{(BR)EBO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector Dark Current	$I_{CEO}$	$V_{CE} = 24\text{V}$	—	10	100	nA
			$V_{CE} = 24\text{V}, T_a = 85^\circ\text{C}$	—	2	50	$\mu\text{A}$
	Collector Dark Current (TLP731)	$I_{CER}$	$V_{CE} = 24\text{V}, T_a = 85^\circ\text{C}$ $R_{BE} = 1\text{M}\Omega$	—	0.5	10	$\mu\text{A}$
	Collector Dark Current (TLP731)	$I_{CBO}$	$V_{CB} = 10\text{V}$	—	0.1	—	nA
	DC Forward Current Gain (TLP731)	$h_{FE}$	$V_{CE} = 5\text{V}, I_C = 0.5\text{mA}$	—	400	—	—
Capacitance Collector to Emitter	$C_{CE}$	$V = 0, f = 1\text{MHz}$	—	10	—	pF	

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	$I_C / I_F$	$I_F = 5\text{mA}, V_{CE} = 5\text{V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_F (\text{sat})$	$I_F = 1\text{mA}, V_{CE} = 0.4\text{V}$ Rank GB	—	60	—	%
			30	—	—	
Base Photo-Current (TLP731)	$I_{PB}$	$I_F = 5\text{mA}, V_{CB} = 5\text{V}$	—	10	—	$\mu\text{A}$
Collector-Emitter Saturation Voltage	$V_{CE} (\text{sat})$	$I_C = 2.4\text{mA}, I_F = 8\text{mA}$ $I_C = 0.2\text{mA}, I_F = 1\text{mA}$ Rank GB	—	—	0.4	V
			—	0.2	—	
			—	—	0.4	

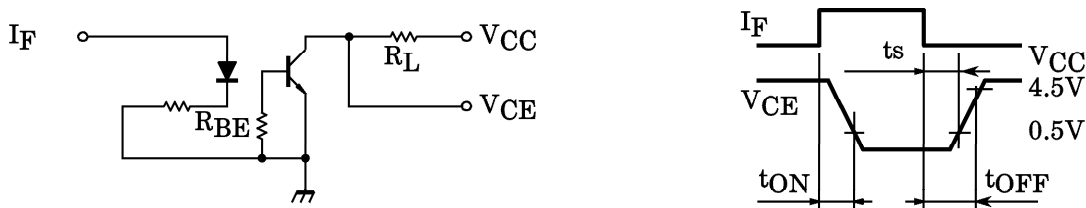
ISOLATION CHARACTERISTICS (Ta = 25°C)

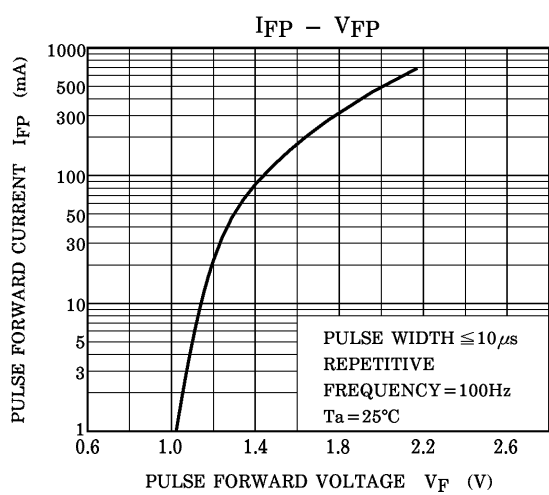
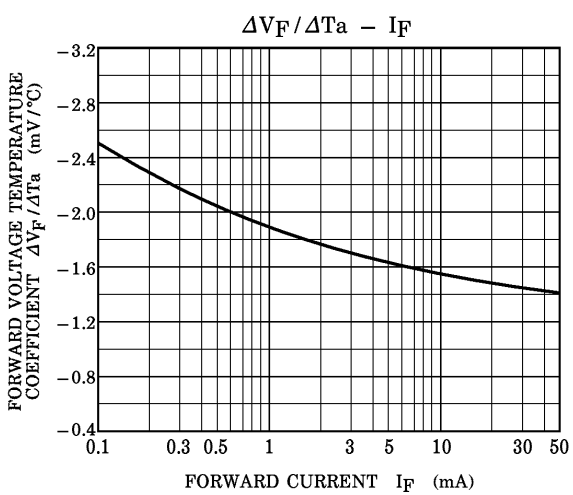
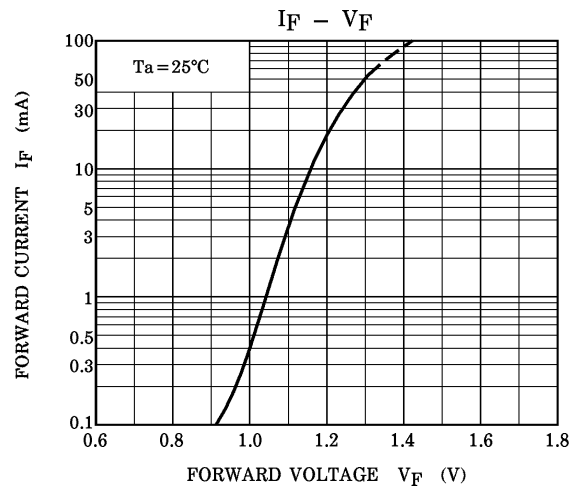
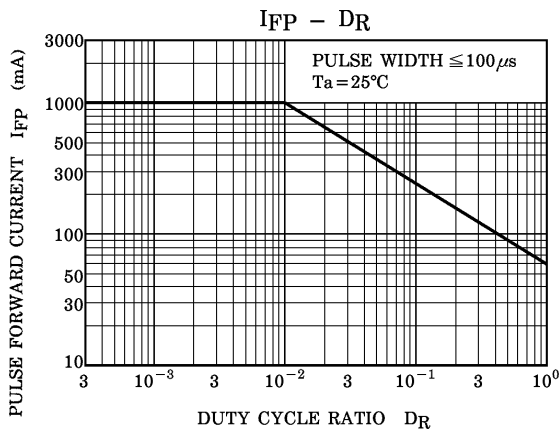
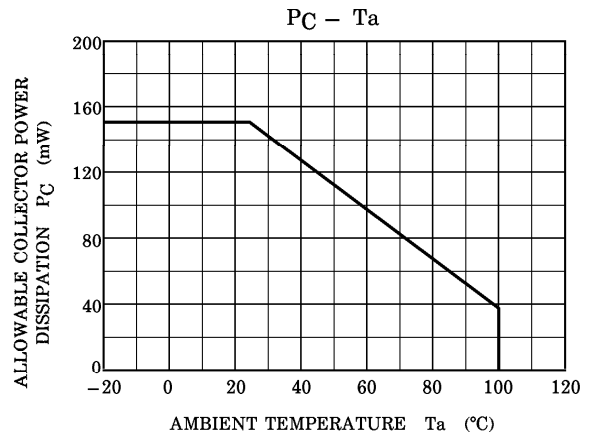
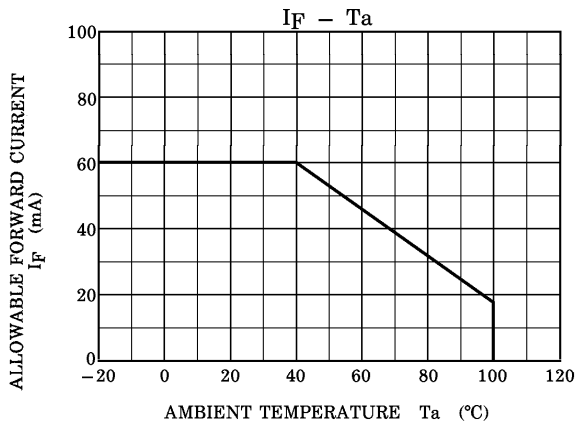
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance (Input to Output)	C <sub>S</sub>	V <sub>S</sub> =0, f=1MHz	—	0.8	—	pF
Isolation Resistance	R <sub>S</sub>	V <sub>S</sub> =500V	1×10 <sup>12</sup>	10 <sup>14</sup>	—	Ω
Isolation Voltage	BV <sub>S</sub>	AC, 1 minute	4000	—	—	V <sub>rms</sub>
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	V <sub>dc</sub>

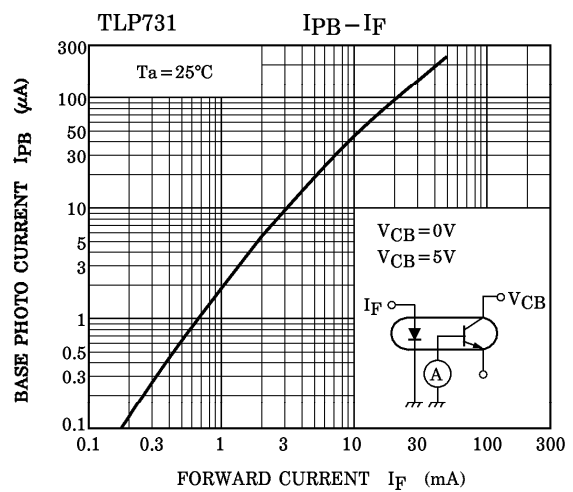
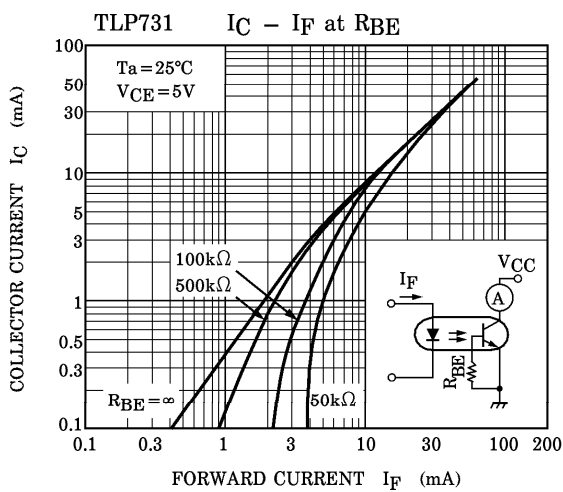
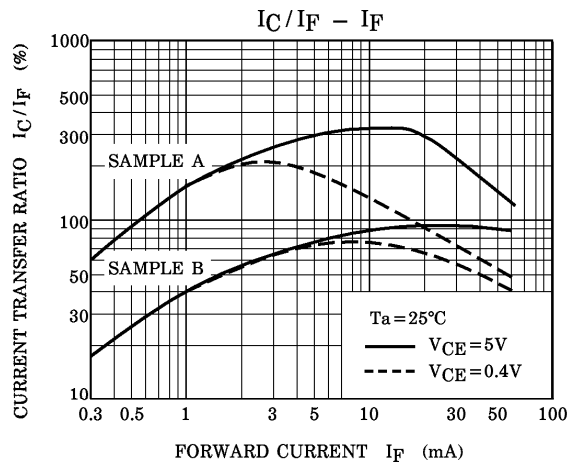
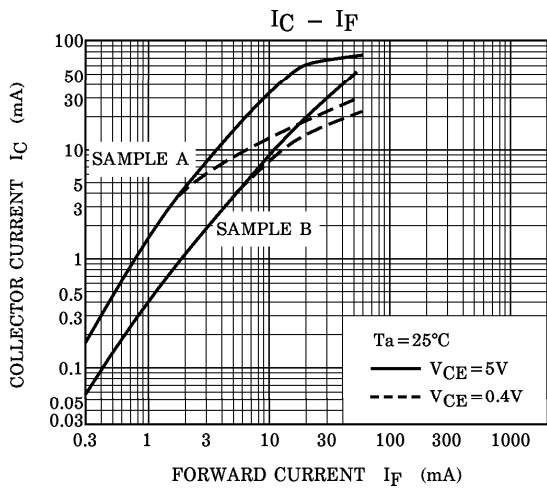
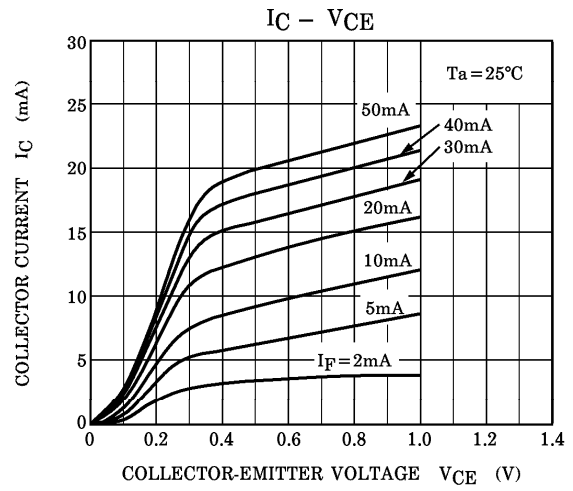
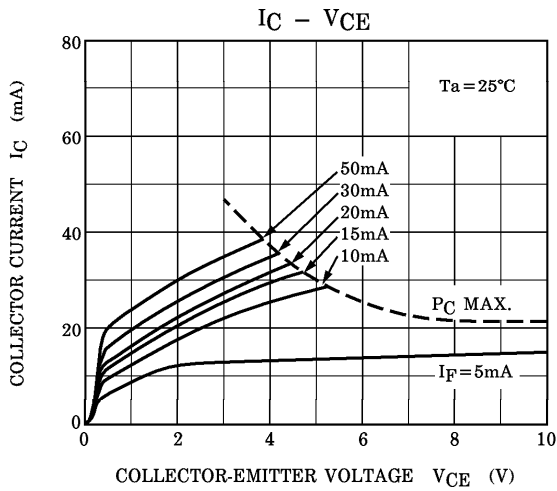
SWITCHING CHARACTERISTICS (Ta = 25°C)

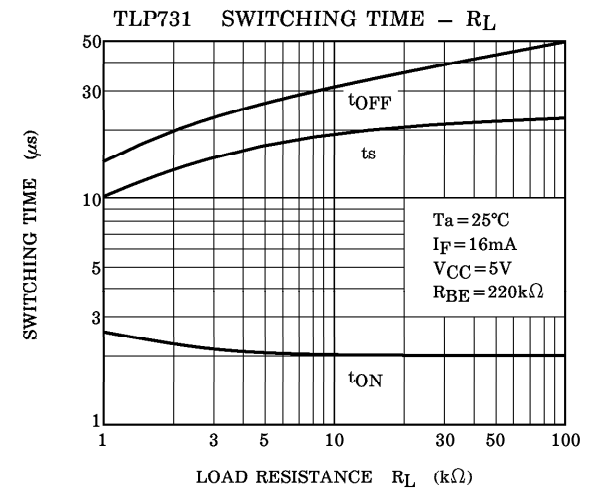
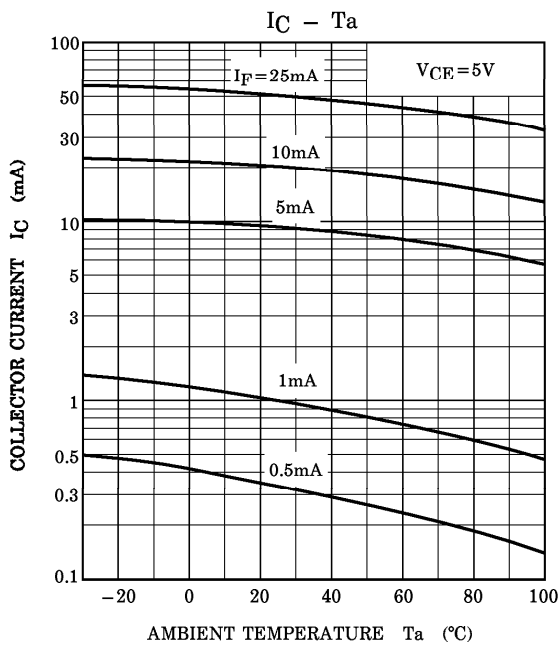
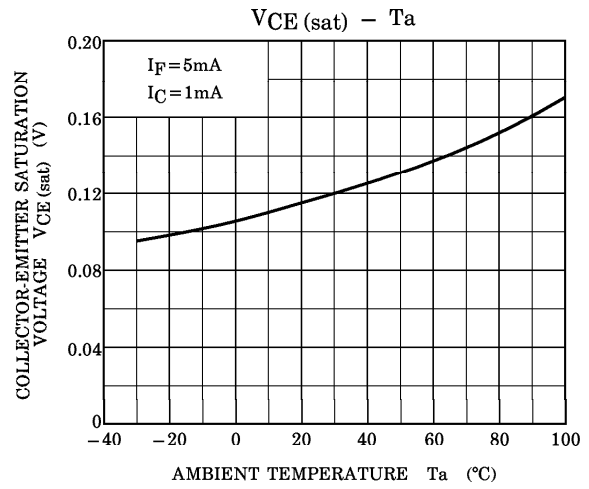
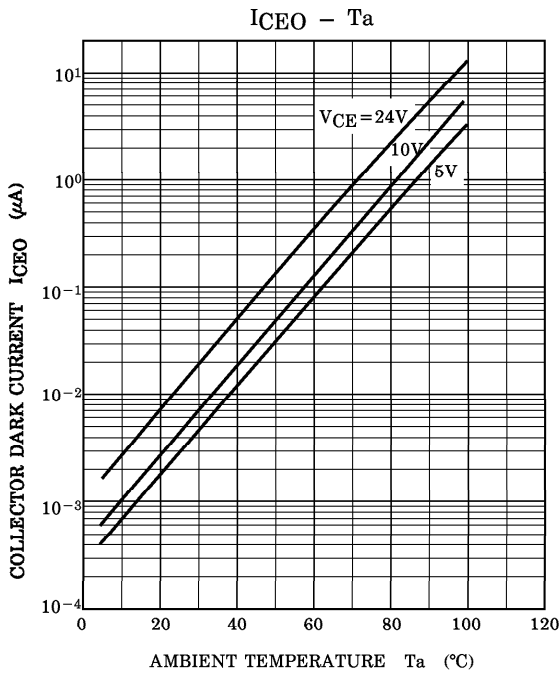
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	t <sub>r</sub>	V <sub>CC</sub> = 10V, I <sub>C</sub> = 2mA R <sub>L</sub> = 100Ω	—	2	—	μs
Fall Time	t <sub>f</sub>		—	3	—	
Turn-on Time	t <sub>on</sub>		—	3	10	
Turn-off Time	t <sub>off</sub>		—	3	10	
Turn-on Time	t <sub>ON</sub>	R <sub>L</sub> = 1.9kΩ (Fig.1) R <sub>BE</sub> = OPEN V <sub>CC</sub> = 5V, I <sub>F</sub> = 16mA	—	2	—	μs
Storage Time	t <sub>s</sub>		—	15	—	
Turn-off Time	t <sub>OFF</sub>		—	25	—	
Turn-on Time	t <sub>ON</sub>	R <sub>L</sub> = 1.9kΩ (Fig.1) R <sub>BE</sub> = 220kΩ (TLP731) V <sub>CC</sub> = 5V, I <sub>F</sub> = 16mA	—	2	—	μs
Storage Time	t <sub>s</sub>		—	12	—	
Turn-off Time	t <sub>OFF</sub>		—	20	—	

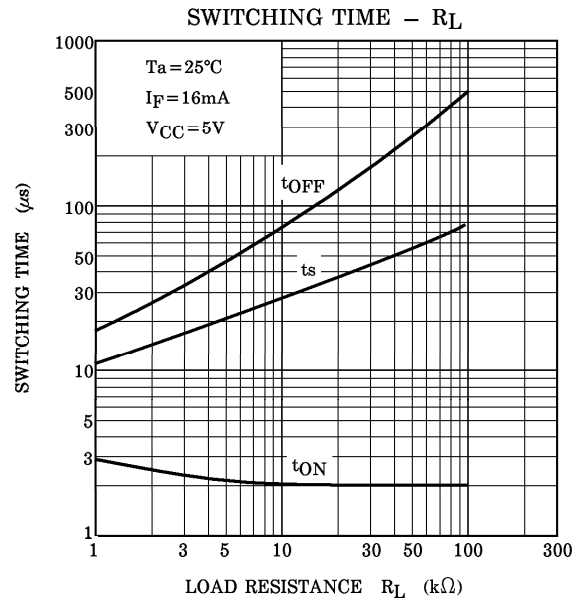
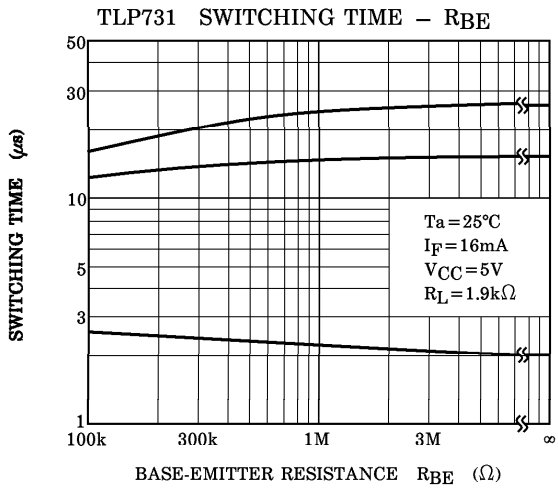
Fig. 1 SWITCHING TIME TEST CIRCUIT













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